

NVMFS5830NL

Power MOSFET

40 V, 2.3 mΩ, 185 A, Single N-Channel

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- NVMFS5830NLWF – Wettable Flanks Product
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	40	V
Gate-to-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current $R_{\Psi J-mb}$ (Notes 1, 2, 3, 4)	Steady State	$T_{mb} = 25^{\circ}\text{C}$	I_D	185	A
		$T_{mb} = 100^{\circ}\text{C}$		131	
Power Dissipation $R_{\Psi J-mb}$ (Notes 1, 2, 3)	Steady State	$T_{mb} = 25^{\circ}\text{C}$	P_D	158	W
		$T_{mb} = 100^{\circ}\text{C}$		79	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 3, 4)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	29	A
		$T_A = 100^{\circ}\text{C}$		20	
Power Dissipation $R_{\theta JA}$ (Notes 1 & 3)	Steady State	$T_A = 25^{\circ}\text{C}$	P_D	3.8	W
		$T_A = 100^{\circ}\text{C}$		1.9	
Pulsed Drain Current	$T_A = 25^{\circ}\text{C}$, $t_p = 10\text{ }\mu\text{s}$		I_{DM}	1012	A
Operating Junction and Storage Temperature			T_J , T_{stg}	-55 to + 175	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	185	A
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^{\circ}\text{C}$, $V_{GS} = 10\text{ V}$, $I_{L(pk)} = 85\text{ A}$, $L = 0.1\text{ mH}$, $R_G = 25\text{ }\Omega$)			E_{AS}	361	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Mounting Board (top) – Steady State (Notes 2, 3)	$R_{\Psi J-mb}$	1.0	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	39	

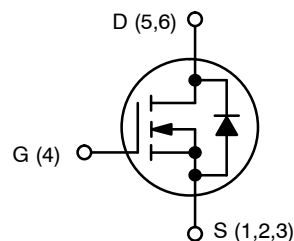
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi (Ψ) is used as required per JESD51-12 for packages in which substantially less than 100% of the heat flows to single case surface.
3. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
4. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



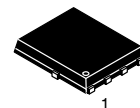
ON Semiconductor®

<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	2.3 mΩ @ 10 V	185 A
	3.6 mΩ @ 4.5 V	

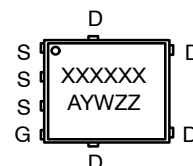


N-CHANNEL MOSFET



DFN5
(SO-8FL)
CASE 488AA
STYLE 1

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NVMFS5830NL

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			32		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}$	$T_J = 25\text{ }^\circ\text{C}$		1	μA
			$T_J = 125^\circ\text{C}$		100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	1.4		2.4	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			7.2		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		1.7	2.3	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		2.6	3.6	
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 10\text{ A}$		38		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 25\text{ V}$		5880		pF
Output Capacitance	C_{OSS}			750		
Reverse Transfer Capacitance	C_{RSS}			500		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 32\text{ V}; I_D = 60\text{ A}$		58		nC
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 32\text{ V}; I_D = 60\text{ A}$		113		nC
Threshold Gate Charge	$Q_{G(TH)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 32\text{ V}; I_D = 60\text{ A}$		5.5		nC
Gate-to-Source Charge	Q_{GS}			19.5		
Gate-to-Drain Charge	Q_{GD}			32		
Plateau Voltage	V_{GP}			3.6		

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 20\text{ V}, I_D = 10\text{ A}, R_G = 2.5\text{ }\Omega$		22		ns
Rise Time	t_r			32		
Turn-Off Delay Time	$t_{d(OFF)}$			40		
Fall Time	t_f			27		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V},$ $I_S = 10\text{ A}$	$T_J = 25^{\circ}\text{C}$		0.74	1.0	V
			$T_J = 125^{\circ}\text{C}$		0.58		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 60\text{ A}$			41		ns
Charge Time	t_a				19		
Discharge Time	t_b				19		
Reverse Recovery Charge	Q_{RR}					33	

5. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

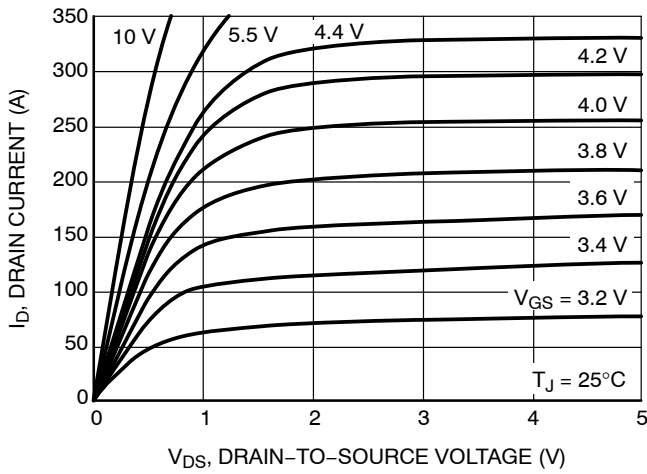


Figure 1. On-Region Characteristics

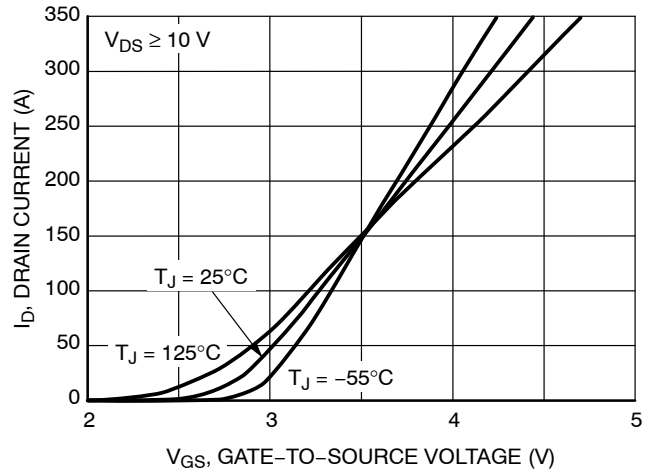


Figure 2. Transfer Characteristics

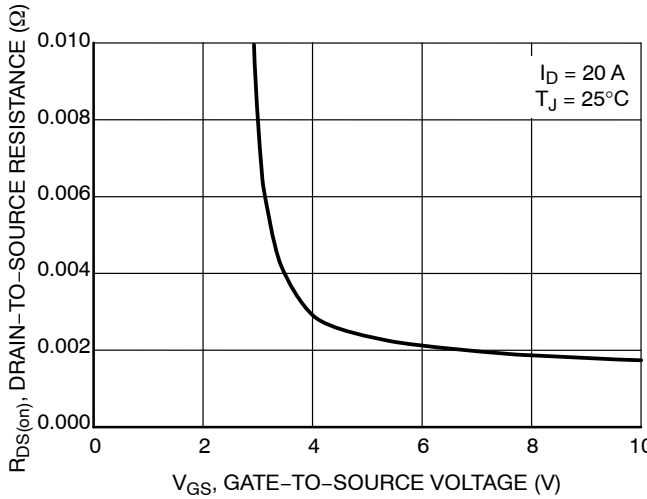


Figure 3. On-Resistance vs. Gate-to-Source Voltage

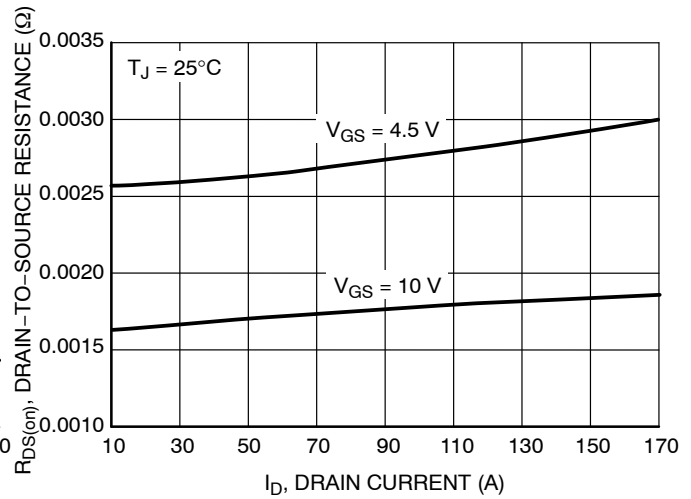


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

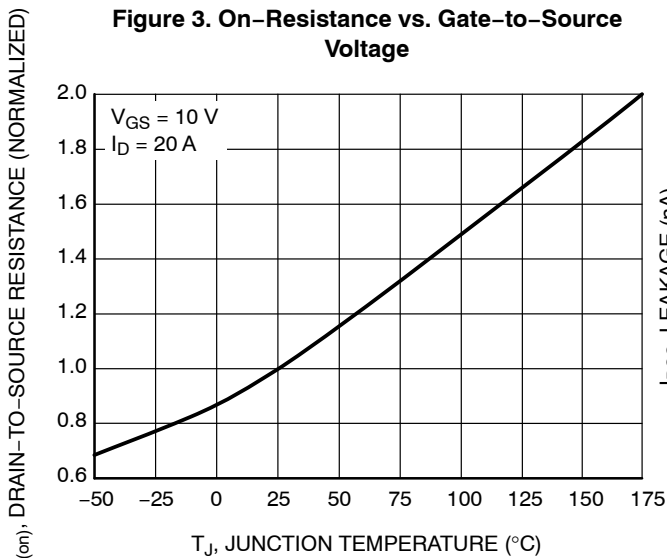


Figure 5. On-Resistance Variation with Temperature

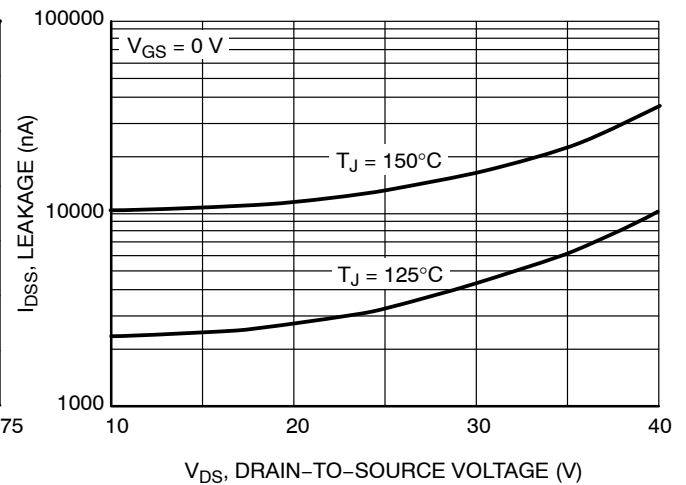


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

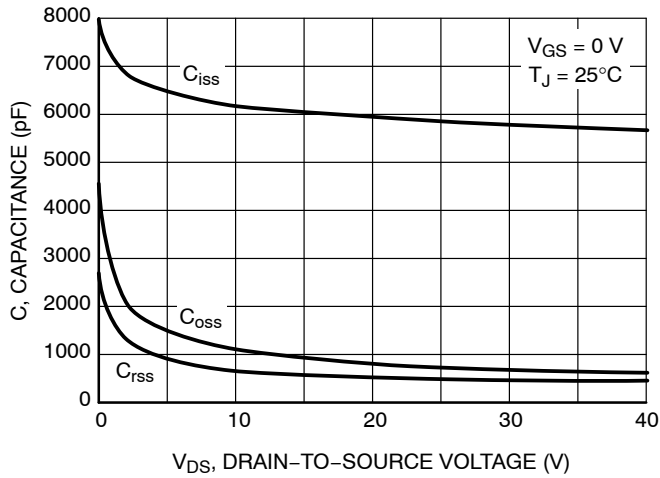


Figure 7. Capacitance Variation

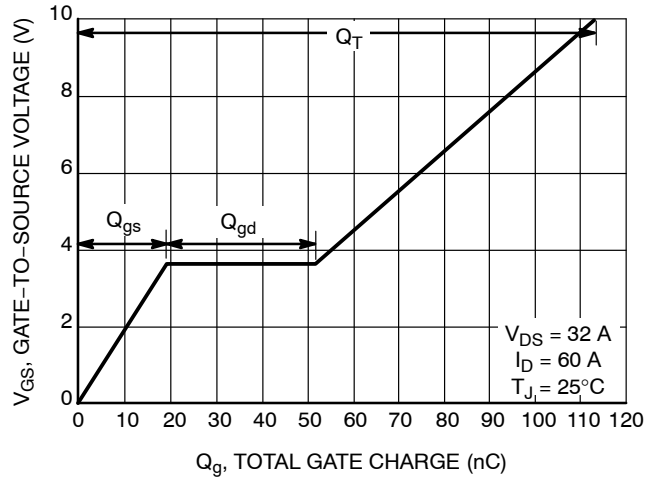


Figure 8. Gate-to-Source Voltage vs. Total Charge

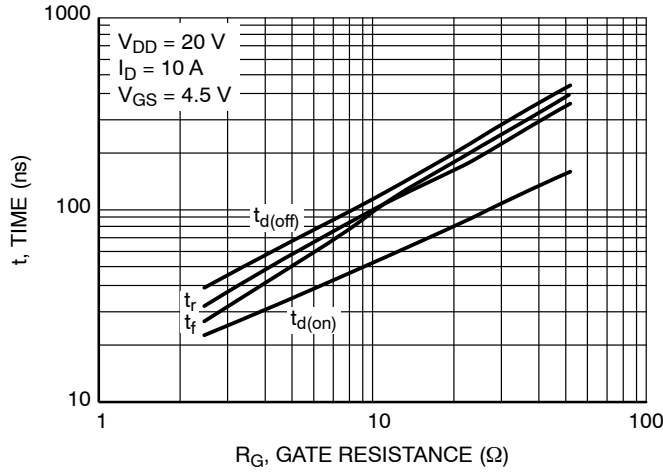


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

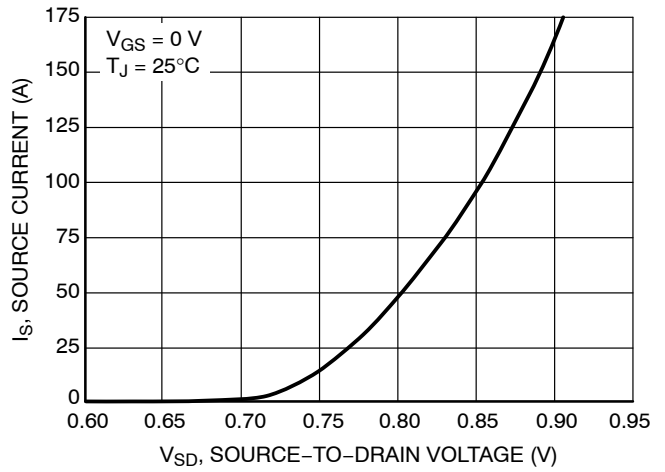


Figure 10. Diode Forward Voltage vs. Current

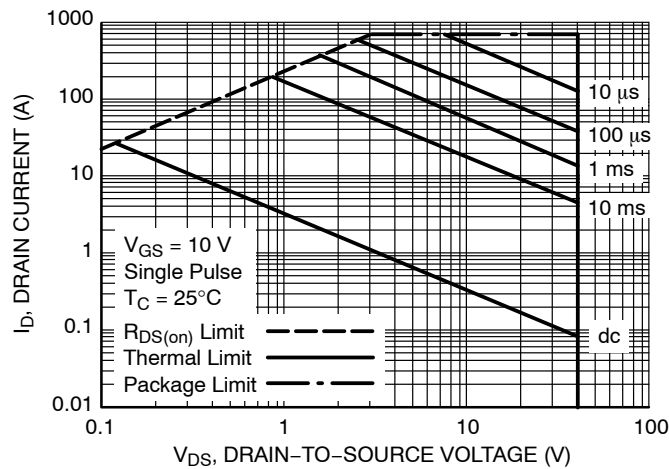


Figure 11. Maximum Rated Forward Biased Safe Operating Area

NVMFS5830NL

TYPICAL CHARACTERISTICS

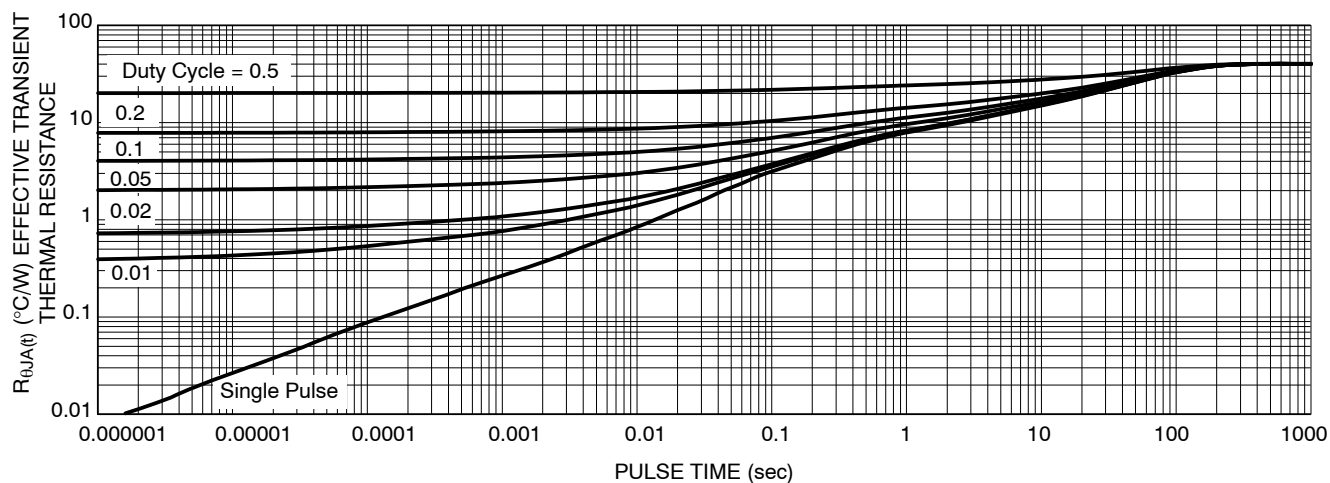


Figure 12. Thermal Response

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NVMFS5830NLT1G	V5830L	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5830NLWFT1G	5830LW	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5830NLT3G	V5830L	DFN5 (Pb-Free)	5000 / Tape & Reel
NVMFS5830NLWFT3G	5830LW	DFN5 (Pb-Free)	5000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



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